

9097250 TOSHIBA (DISCRETE/OPTO)

56C 7559 DT-33-09

**2SC2562**

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

## HIGH CURRENT SWITCHING APPLICATIONS.

## FEATURES:

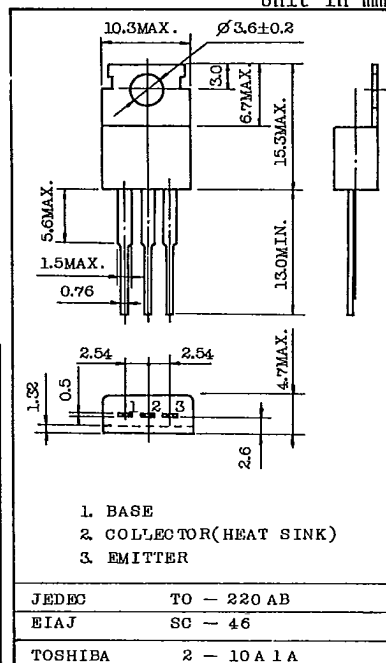
- Low Collector Saturation Voltage :  
 $V_{CE(sat)}=0.4V$  (Max.) (at  $I_C=3A$ )
- High Speed Switching Time :  $t_{stg}=1.0\mu s$  (Typ.)
- Complementary to 2SA1012.

MAXIMUM RATINGS ( $T_a=25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	5	A
Collector Power Dissipation ( $T_c=25^\circ C$ )	$P_C$	25	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ C$

## INDUSTRIAL APPLICATIONS

Unit in mm

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Mounting Kit No. AC75

Weight : 1.9g

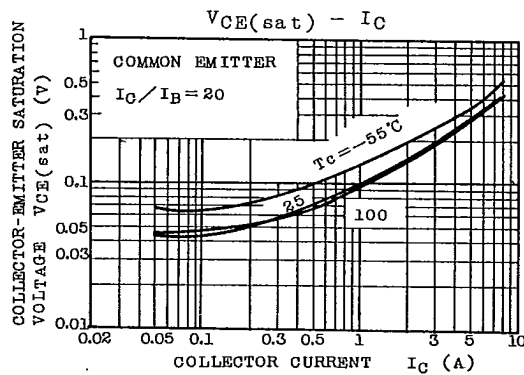
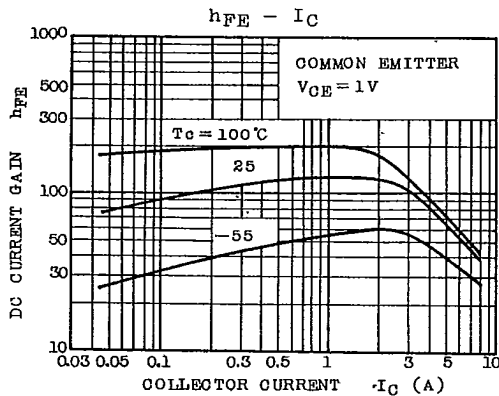
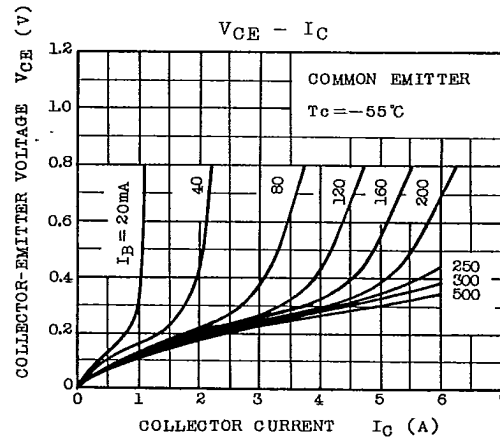
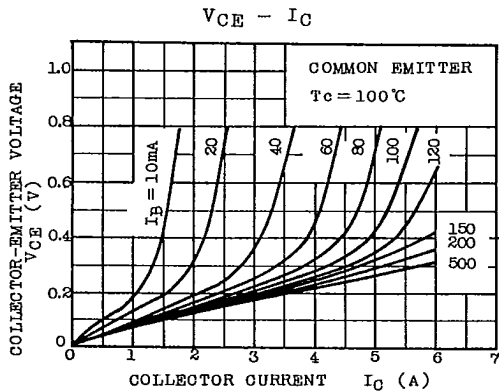
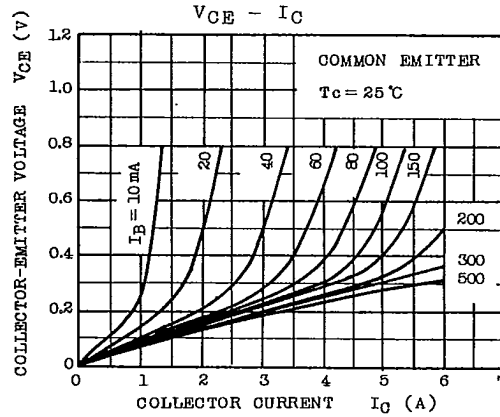
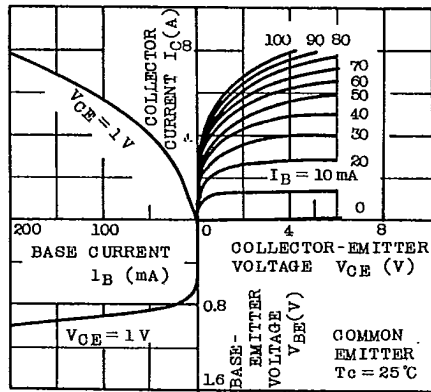
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB}=50V, I_E=0$	-	-	1	$\mu A$
Emitter Cut-off Current		$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	1	$\mu A$
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	50	-	-	V
DC Current Gain		$h_{FE(1)}$ (Note)	$V_{CE}=1V, I_C=1A$	70	-	240	
		$h_{FE(2)}$	$V_{CE}=1V, I_C=3A$	30	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C=3A, I_B=0.15A$	-	0.2	0.4	V
	Base-Emitter	$V_{BE(sat)}$	$I_C=3A, I_B=0.15A$	-	0.9	1.2	
Transition Frequency		$f_T$	$V_{CE}=4V, I_C=1A$	-	120	-	MHz
Collector Output Capacitance		$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$	-	80	-	pF
Switching Time	Turn-on Time	$t_{on}$		-	0.1	-	$\mu s$
	Storage Time	$t_{stg}$		-	1.0	-	
	Fall Time	$t_f$		$I_{B1}=-I_{B2}=0.15A$ DUTY CYCLE $\leq 1\%$	-	0.1	

Note :  $h_{FE(1)}$  Classification 0 : 70~140, Y : 120~240

TOSHIBA CORPORATION

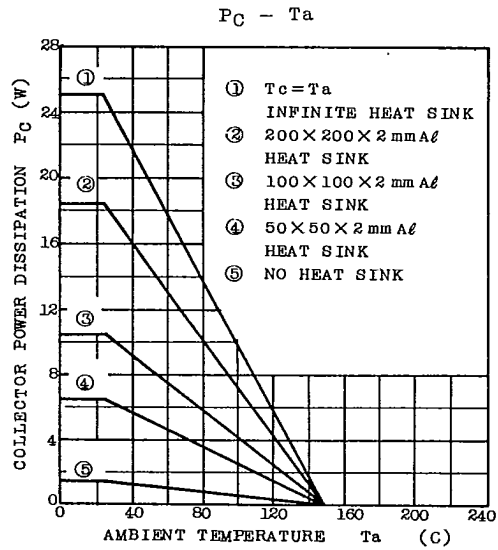
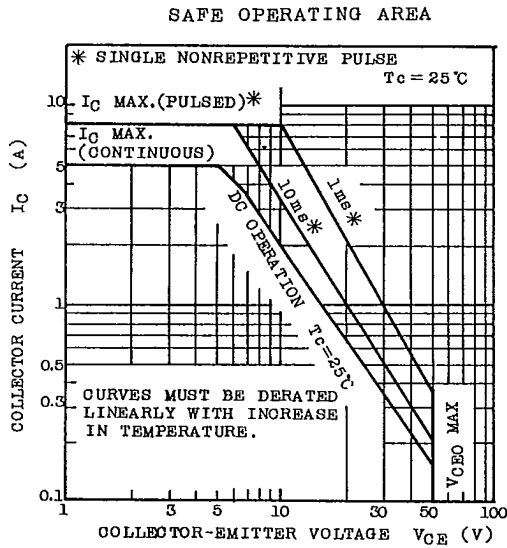
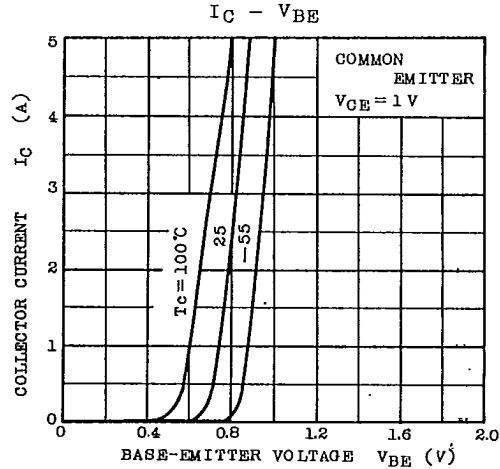
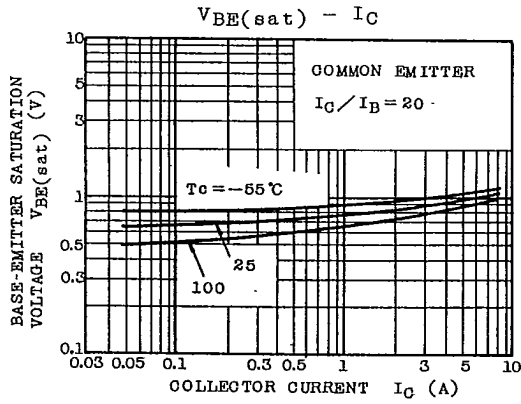
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STATIC CHARACTERISTICS



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